



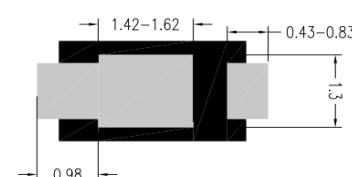
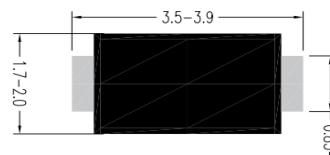
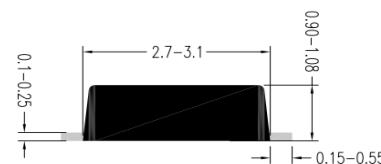
## Surface Mount Schottky Rectifier

### Features

- Low profile package
- Ideal for automated placement
- Guardring for overvoltage protection
- Low power losses, high efficiency
- High forward surge capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

SOD-123HE

Unit : inch(mm)



### Typical Applications

For use in low voltage high frequency inverters, freewheeling, DC/DC converters, and polarity protection applications.

### Mechanical Data

- **Package:** SOD-123HE  
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** Cathode line denotes the cathode end

### ■Maximum Ratings ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	S12HE	S13HE	S14HE	S15HE	S16HE	S18HE	S110HE	S115HE	S120HE
Repetitive peak reverse voltage	VRMM	V	20	30	40	50	60	80	100	150	200
Average rectified output current @60Hz sine wave, Resistance load, $T_a$ (FIG.1)	IO	A						1.0			
Surge(non-repetitive)forward current @60Hz half-sine wave, 1 cycle, $T_j=25^\circ\text{C}$	IFSM	A						30			
Storage temperature	Tstg	°C						-55 ~+150			
Junction temperature	T <sub>j</sub>	°C					-55 ~+150		-55 ~+175		

### ■Electrical Characteristics ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	S12HE	S13HE	S14HE	S15HE	S16HE	S18HE	S110HE	S115HE	S120HE
Maximum instantaneous forward voltage drop per diode	VF	V	IFM=1.0A	0.50		0.65		0.80		0.85		
Maximum DC reverse current at rated DC blocking voltage per diode @ VRM=VRMM	IRRM	mA	T <sub>a</sub> =25°C	0.10					0.05			
			T <sub>a</sub> =100°C	10					5			



■ Thermal Characteristics ( $T_a=25^\circ\text{C}$  Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	S12HE	S13HE	S14HE	S15HE	S16HE	S18HE	S110HE	S115HE	S120HE
Thermal Resistance	R <sub>θJ-A</sub>	°C/W	70 <sup>1)</sup>								
	R <sub>θJ-L</sub>		20 <sup>1)</sup>								

Note:

(1) Thermal resistance between junction and ambient and between junction and lead mounted on P.C.B with 3mm\*3mm copper pad areas.

■ Characteristics (Typical)

FIG1:Io-TLCurve

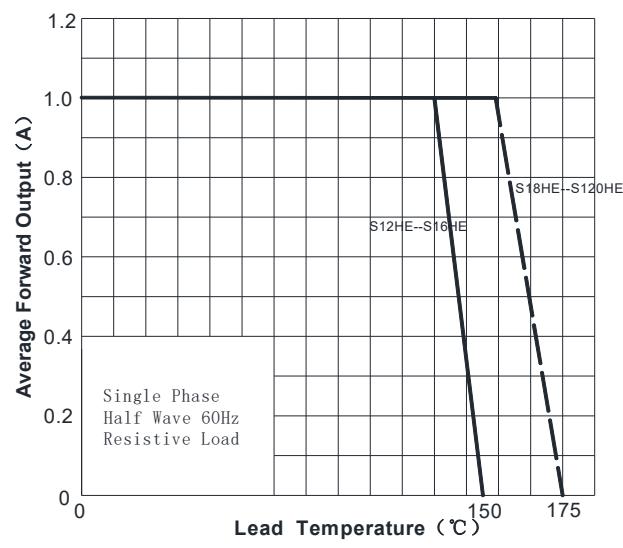


FIG2: Surge Forward Current Capability

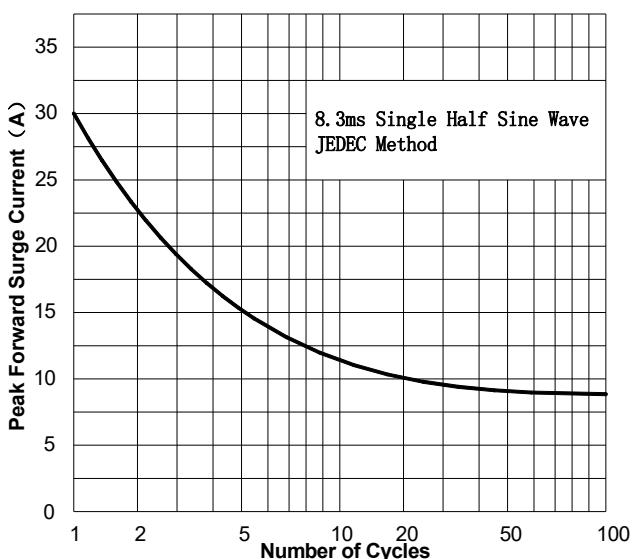


FIG3: Forward Voltage

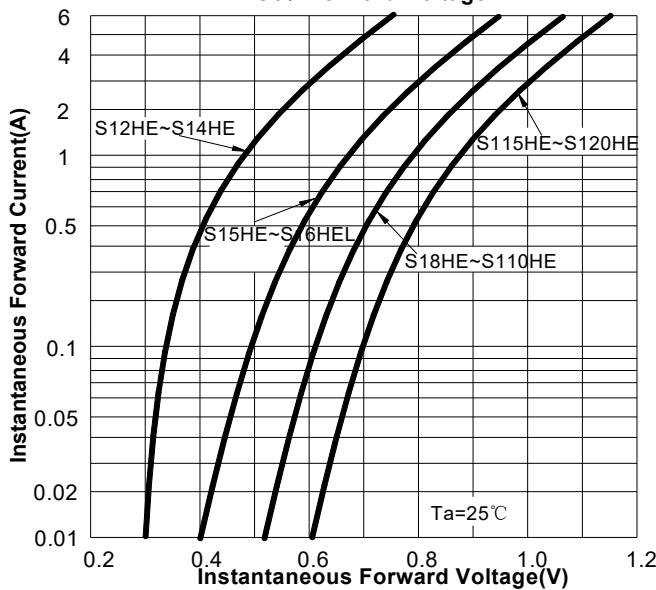


FIG4: Typical Reverse Characteristics

